

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a MOS transistor incorporating a silicon oxide film serving as a gate insulating film and containing nitrogen and a
5 polycrystalline silicon film serving as a gate electrode and containing a dopant and arranged such that the gate electrode is formed on the gate electrode insulating film, and an oxidation process using ozone is performed to sufficiently round the shape of the
10 lower edge of the gate electrode.

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